PROCEEDINGS OF SPIE

Metrology, Inspection, and Process Control XXXVIII

Matthew J. Sendelbach Nivea G. Schuch Editors

26–29 February 2024 San Jose, California, United States

Sponsored by SPIF

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Published by SPIE

Volume 12955

Part One of Two Parts

Proceedings of SPIE 0277-786X, V. 12955

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Metrology, Inspection, and Process Control XXXVIII, edited by Matthew J. Sendelbach, Nivea G. Schuch, Proc. of SPIE Vol. 12955, 1295501 · © 2024 SPIE 0277-786X · doi: 10.1117/12.3031880

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Please use the following format to cite material from these proceedings: Author(s), "Title of Paper," in *Metrology, Inspection, and Process Control XXXVIII*, edited by Matthew J. Sendelbach, Nivea G. Schuch, Proc. of SPIE 12955, Seven-digit Article CID Number (DD/MM/YYYY); (DOI URL).

ISSN: 0277-786X

ISSN: 1996-756X (electronic)

ISBN: 9781510672161

ISBN: 9781510672178 (electronic)

Published by

SPIE

P.O. Box 10, Bellingham, Washington 98227-0010 USA Telephone +1 360 676 3290 (Pacific Time)

SPIE.org

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